

## ABSTRACT OF THE DISCLOSURE

A method for manufacturing a SiC device embraces (a) depositing a polysilicon film above a SiC substrate; (b) delineating the  
5 polysilicon film into required pattern; and (c) annealing the SiC  
substrate in a water rich ambient to selectively grow a thick localized  
thermal oxide film above the SiC substrate. At the surface of SiC  
substrate, source/drain regions and substrate contact region are  
formed. In the water rich ambient, the H<sub>2</sub>O partial pressure is so  
10 maintained that it is more than 0.95.